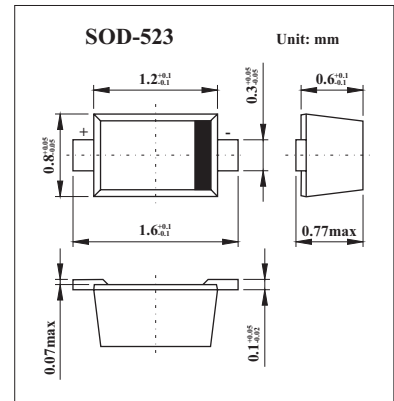


Schottky barrier diode

1PS79SB31

■ Features

- Very Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V_R			30	V
continuous forward current	I_F			200	mA
repetitive peak forward current	I_{FSM}	$t_p \leq 1\text{s}; \delta \leq 0.5$		300	mA
non-repetitive peak forward current	I_{FSM}	$t = 8.3\text{ ms half sinewave};$ JEDEC method		1000	mA
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			125	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Typ	Max	Unit
forward voltage	V_F	$I_F = 0.1\text{ mA}$	130	190	mV
		$I_F = 1\text{ mA}$	190	250	
		$I_F = 10\text{ mA}$	255	300	
		$I_F = 100\text{ mA}$	355	410	
		$I_F = 200\text{ mA}$	420	500	
capacitance reverse current	I_R	$V_R = 10\text{ V}, \text{ note 1};$	2.5	30	$\mu\text{ A}$
diodes capacitance	C_d	$V_R = 1\text{ V}, f = 1\text{ MHz};$	20	25	pF

Note

1. Pulse test: pulse $t_p = 300\ \mu\text{s}$, $\delta = 0.02$.

■ Marking

Marking	G3
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